

**REMARKS**

Claims 3, 4, 7 and 8 have been amended. New claims 17-26 have been added. Accordingly, claims 3, 4, 7, 8, 11, 12 and 15-26 are currently pending in the application.

**PRIORITY**

Applicants request the Examiner to acknowledge the claim for priority and safe receipt of the certified priority document.

**35 U.S.C. §102**

Claims 3, 4, 7 and 8 stand rejected under 35 U.S.C. §102 as being anticipated by Hase et al. This rejection is traversed as follows.

The present application has overlapping inventive entities to the newly discovered reference to Hase et al. However, there is an important difference between the present invention and Hase et al. Namely, in the present invention, a part 35 of ground metal 19 on the surface of the second-layer dielectric substrate is removed without creating a hole or aperture through dielectric substrate 18 (see Fig. 1 and page 11, lines 10-14, for example). The same applies to Figures

5A, 6A, 7A and 8A and their corresponding description. On the other hand, Hase et al disclose that dielectric substrate 18 has a hole or aperture 35.

The present inventors have discovered that when a hole such as that taught by Hase et al is present, bending of the portion of the substrate above the hole onto which a high frequency circuit element is mounted results. Therefore, if conductor line 9 of the matching circuit on the output side of the surface of the first layer dielectric substrate 1 is placed over such a hole, bending of the substrate will result. This changes the impedance of the high frequency circuit and, in a worst case scenario, could cause a break in the circuit.

Therefore, according to the present invention, a portion of the ground metal is removed while the dielectric substrate below this removed portion is maintained. This way, the bending problem in the prior art is avoided. As such, it is submitted the pending claims patentably define the present invention over the cited art.

#### **REQUEST FOR INTERVIEW**

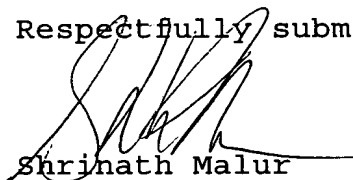
Applicants request the Examiner to conduct an interview with the undersigned in order to clarify the points raised above in order to speed the prosecution of the application.

The Examiner is invited to contact the undersigned by telephone in order to arrange an appropriate time for the interview.

**CONCLUSION**

In view of the foregoing amendments and remarks, Applicants contend that the above-identified application is now in condition for allowance. Accordingly, reconsideration and reexamination are respectfully requested.

Respectfully submitted,



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**MARKED UP VERSION OF REPLACED  
PARAGRAPHS OF THE SPECIFICATION**

**Page 6, third full paragraph (lines 13-19), the marked up paragraph is as follows:**

Specifically [Concretely], to thicken a dielectric [substance] substrate that ranges between the conductor forming the transmission line of the matching circuit on the side of input or output and the ground metal, the ground metal provided to the dielectric substrate between them is formed in the shape in which a part is hollowed out so that a part opposite to the conductor is included.

**Page 7, fifth, sixth and seventh full paragraphs (lines 14-22), the marked up paragraphs are as follows:**

Figs. 5A and 5B are an exploded view and a sectional view showing a high frequency circuit module equivalent to a second embodiment of the invention;

Figs. 6A and 6B are an exploded view and a sectional view showing a high frequency circuit module equivalent to a third embodiment of the invention;

Figs. 7A and 7B are an exploded view and a sectional view showing a high frequency circuit module equivalent to a fourth embodiment of the invention;

**MARKED UP VERSION OF REWRITTEN CLAIMS**

3. (Amended) A high frequency circuit module provided with a [two- or more-layer] first dielectric substrate[,] on which a semiconductor element and matching circuits on the input side and on the output side respectively of the semiconductor element respectively formed, [on the dielectric substrate, and] a first ground metal plate, and one or more second dielectric substrates located between said first dielectric substrate and the first ground metal, wherein:

a second ground metal is provided on the surface of each of the second dielectric substrates, and the second ground metal provided on the surface of at least one of the second dielectric substrates being adjacent to the first dielectric substrate is formed in the shape in which a part of the second ground metal opposite to the transmission line of said matching circuit on the output side is removed while maintaining the dielectric substrate adjacent to the part of the second ground metal that is removed [to the dielectric substrate existing between a conductor of transmission line of said matching circuit on the output side and said ground metal is formed in the shape in which a part is hollowed out so that

a part opposite to said conductor transmission line is included].

4. (Amended) A high frequency circuit module according to Claim 3, wherein:

said second ground metal [provided to the dielectric substrate existing between said conductor of transmission line of said matching circuit on the input side and said ground metal] is formed in the shape in which a part [is hollowed out so that a part] opposite to said [conductor of said] transmission line of said matching circuit on the input side is removed while maintaining the dielectric substrate adjacent to the part removed [is included].

7. (Amended) A high frequency circuit module provided with a [two- or more-layer] first dielectric substrate[, ] on which a semiconductor element and matching circuits on the input side and on the output side respectively of the semiconductor element respectively formed, [on the dielectric substrate, and] a first ground metal plate, and one or more second dielectric substrates located between said first dielectric substrate and the first ground metal, wherein:

a second ground metal [provided to the dielectric substrate existing between a conductor of transmission line of said matching circuit on the input side and said ground metal] is provided on the surface of each of the second dielectric substrates, and the second ground metal provided on the surface of at least one of the second dielectric substrates being adjacent to the first dielectric substrate is formed in the shape in which a part of the second ground metal opposite to the transmission line of said matching circuit on the input side is removed while maintaining the dielectric substrate adjacent to the part of the second ground metal that is removed [formed in the shape in which a part is hollowed out so that a part opposite to said conductor transmission line is included].

8. (Amended) A high frequency circuit module according to Claim 7, wherein:

the second ground metal [provided to the dielectric substrate existing between said conductor of transmission line of said matching circuit on the output side and said ground metal] is formed in the shape in which a part opposite to said transmission line of said matching circuit on the output side is removed while maintaining the dielectric substrate adjacent

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to the part removed [is hollowed out so that a part opposite to said conductor of said transmission line is included].